CHARACTERIZATION OF GRAPHENE FILMS USING TERAHERTZ IMAGING AND SPECTROSCOPY

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Graphene has received significant attention due to its many unique properties, such as its twodimensionality, zero-mass and zero-gap band structure, and unsurpassed strength. Additionally, its terahertz (THz) properties are being studied for future ultrafast electronics for information and communication, sensing and other applications. However, the basic properties of graphene in the presence of THz radiation are largely unexplored, although many theoretical studies exist. In this study, we explore the THz dynamics of graphene on indium phosphide (InP) and magnesium oxide (MgO) substrates, using THz time domain spectroscopy (THz-TDS) and laser terahertz emission microscopy (LTEM). Using LTEM, we compared the THz radiation from InP to the radiation through graphene on InP to find that graphene decreases the amplitude of THz. Furthermore, we investigated the effect of continuous wave (cw) lasers of different wavelengths on THz radiation and discovered that a 365 nm cw laser greatly decreased THz transmittance through graphene on InP, but an 800 nm cw laser had no effect, proving wavelength dependence of THz generation. We also studied the spatial variation of THz absorption of graphene on InP and MgO substrates using an LTEM system with THz-TDS, which allowed us to visualize the localized transmittance distribution of graphene. Both THz-TDS and LTEM results help us understand THz functionality in graphene on InP and MgO in order to develop future electronics.

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Field

0.005



Purpose

Motivation: Characterize and understand the terahertz (THz) dynamics of graphene for future applications. Graphene on InP is largely unexplored. InP has high emobility (5400 cm²/(V*s) at 300 K) and a direct band gap.

Goals:

•Characterize graphene on InP •Study the interface effects of graphene Look at the effect of continuous wave lasers



Background

Terahertz :

- Frequency range= 300GHz to 30 THz.
- Wavelength 1 mm to 10 micrometers
- Terahertz-Time Domain Spectroscopy (TDS) measures the transmitted electric field. Fourier transform gives frequency spectrum.
- Laser Terahertz Emission Microscopy (LTEM) measures the near field absorption of the



Graphene:

Single-layer graphene

- Fabrication by chemical vapor deposition (CVD) Astounding properties: single layer
- semiconductor, zero bandgap, strongest and stiffest material, high mobility, lowest resistivity
- 2.3% interband absorbance
- Applications: information and communication, sensing, ultrafast electronics, transistors, inert coatings, biodevices

graphene Double-layer graphene Conduction band



- with and without 365 nm cw laser and 800 nm cw laser
- Reflection type setup: **Emission**
- THz generated by InP substrate
- Surge current/ surface field effect
- Galvano meter for raster scanning
- DASC crystal instead of substrate emitter
- Transmission type— measured **transmittance** of graphene on MgO and InP
- Optical rectification, 1.56 micron laser

0.020 -

0.015 -

• Peak amplitude monitored over time with cw laser



800.0

System 1/Emission: Greater decrease on graphene System 2/Transmission: Greater decrease on InP 1. Although the 365 nm laser clearly effects the THz emission and transmittance, we cannot determine if this effect is from graphene or InP because emission (system 1) and transmission (system 2) results are contraversial.

2.Continue experiments with cw laser on InP only and graphene on InP to understand the strange cw laser effects and its effect on transmission vs emission.

Conclusions

1. Graphene effects surge current mechanism on InP, decreasing THz emission.

Gra+InP 365 nm laser

- InpP 365 nm laser

Gra+InP

- 2. We can see the local distribution of the surface of CVD graphene using an LTEM system.
- 3. A 365 nm laser clearly affects THz emission mechanism.

References

Inoue, Ryotaro, Kazuhisa Takayama, and Masayoshi Tonouchi. "Angular Dependence of Terahertz Emission from Semiconductor Surfaces Photoexcited by Femtosecond Optical Pulses." Journal of the Optical

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Results A (System 1)

1. THz emission decreases more than expected in the presence of graphene on InP. Frequency Response



Society of America B 26.9 (2009): A14. Print.

Serita, Kazunori, S. Mizuno, H. Murakami, I. Kawayama Y. Takahashi, M. Yoshimura, Y. Mori, J. Darma, and M. Tonouchi. "Scanning Laser Terahertz Near-field Imaging System." Optics Express 163639th ser. 20.12 (2012): 1 7. Print.

Suzuki, Masato, Masayoshi Tonouchi, Ken-ichi Fujii, Hideyuki Ohtake, and Tomoya Hirosumi. "Excitation Wavelength Dependence of Terahertz Emission from Semiconductor Surface." *Applied Physics Letters* 89.9 (2006): 091111. Print.